

IN THE CLAIMS

This listing of claims replaces all prior versions and listings of claims:

1. (Currently Amended) A solid-state imaging device comprising:

an imaging area having a plurality of unit cells in a two-dimensional array, each unit cell of the plurality of unit cells including a group of a predetermined number of pixels;

a plurality of signal lines to select the pixels including a full-face signal line and a reset signal line, wherein each unit cell includes a plurality of photoelectric converters corresponding to the pixels;

an amplifying unit shared by the pixels to amplify a signal readout from each photoelectric converter and output an amplified readout signal; and

a supply element to supply the readout signal to the amplifying unit,

wherein,

the signal line used to drive the amplifying unit is the full-face signal line shared by the pixels and driving the full-face signal line allows the signal to be read out from each pixel, and

the full-face signal line surrounds each of the plurality of unit cells, serves as a light shielding film, and has an opening corresponding to a light receiving surface for every pixel.

2. (Previously Presented) The solid-state imaging device according to claim 1, further comprising:

a reset unit to reset an input section of the amplifying unit when a reset signal is supplied by the reset signal line.

3. (Cancelled)

4. (Withdrawn) The solid-state imaging device according to claim 1, wherein the unit cells are shifted from each other in the column direction by one pixel or by an amount smaller than one pixel for every pixel column in the imaging area.

5. (Previously Presented) The solid-state imaging device according to claim 2, further comprising:

a full-face selection signal that passes through the full-face signal line to drive the reset unit and the amplifying unit,

wherein,

the full-face selection signal is changed from an active state to a non-active state at a time outside a readout operation period of the pixel.

6. (Previously Presented) The solid-state imaging device according to claim 2, wherein the reset unit is a transistor, and

wherein a full-face selection signal passing through the full-face signal line is changed to an active state during a readout period of the pixel, the reset signal supplied to a gate of the reset unit through the reset signal line is changed to a non-active state, and a driving signal supplied to a transfer unit through a transfer signal line is changed to the active state to read out a charge signal stored in the photoelectric converter.

7. (Withdrawn) A solid-state imaging device comprising
an imaging area having a plurality of unit cells in a two-dimensional array, each unit cell including a group of a predetermined number of pixels; and

signal lines used for selecting the pixels,

wherein the unit cell includes a plurality of photoelectric converters corresponding to the pixels; amplifying means, shared by the pixels, for amplifying a signal read out from each photoelectric converter and outputting the amplified signal; and

transfer means for selectively reading out the signal from the photoelectric converter and supplying the readout signal to the amplifying means, and

wherein the photoelectric converters in the unit cells are arranged so as to be diagonally adjacent to each other.

8. (Withdrawn) The solid-state imaging device according to claim 7, wherein the photoelectric converters diagonally adjacent to each other are horizontally or vertically shifted by an amount smaller than one pixel.

9. (Withdrawn) The solid-state imaging device according to claim 7, wherein the signal line used for driving the amplifying means is a full-face signal line shared by all the pixels and driving the full-face signal line allows the signal to be read out from each pixel.

10. (Withdrawn) The solid-state imaging device according to claim 9, further comprising reset means for resetting an input section of the amplifying means.

11. (Withdrawn) The solid-state imaging device according to claim 10, wherein the signal line used for driving the reset means is the full-face signal line and driving the full-face signal line resets the input section of the amplifying means.

12. (Withdrawn) The solid-state imaging device according to claim 7, wherein signals output from the pixels in the imaging area are read out through two output systems.

13. (Withdrawn) The solid-state imaging device according to claim 12, wherein the imaging area is provided with a RGB Bayer color filter, and wherein signals are read out from the pixels filtered by G filters through the same output system.

14. (Withdrawn) The solid-state imaging device according to claim 10, wherein a full-

face selection signal passing through the full-face signal line used for driving the reset means and the amplifying means is changed from an active state to a non-active state at a time outside a readout operation period of the pixel.

15. (Withdrawn) The solid-state imaging device according to claim 10, wherein the reset means is a transistor, and wherein a full-face selection signal passing through the full-face signal line is changed to an active state during a readout period of the pixel, a reset signal supplied to the gate of the reset means is changed to a non-active state, and a driving signal supplied to the transfer means is changed to the active state to read out a charge signal stored in the photoelectric converter.

16-20. (Cancelled)

21. (Previously Presented) The solid-state imaging device according to claim 2, wherein the full-face signal line is connected to drains of the reset unit and the amplifying unit.

22. (Previously Presented) The solid-state imaging device according to claim 1, wherein the reset signal line controls a voltage supplied to a gate of a reset unit.

23. (Previously Presented) The solid-state imaging device according to claim 1, further comprising:

at least one transfer signal line to control at least one transfer unit.

24. (New) A solid-state imaging device comprising:

an imaging area having a plurality of unit cells in a two-dimensional array, each unit cell of the plurality of unit cells including a group of a predetermined number of pixels;

signal lines to select the pixels, wherein each unit cell includes a plurality of photoelectric converters corresponding to the pixels;

an amplifying unit shared by the pixels to amplify a signal readout from each photoelectric converter and output an amplified readout signal;

a supply element to supply the readout signal to the amplifying unit; and

a full-face signal line connected to drains of the reset unit and the amplifying unit, wherein,

a full-face selection signal passing through the full-face signal line is changed between an active state and a non-active state.

25. (New) The solid-state imaging device according to claim 24, further comprising:

a reset transistor to reset an input section of the amplifying unit when a reset signal is supplied by the reset signal line,

wherein,

the full-face selection signal is changed to an active state during a readout period of the pixel, the reset signal supplied to a gate of the reset unit through the reset signal line is changed to a non-active state, and a driving signal supplied to a transfer unit through a transfer signal line is changed to the active state to read out a charge signal stored in the photoelectric converter.